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1st Reading

Alcohol vapor sensing by cadmium-doped zinc oxide thick films based chemical sensor

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Cadmium doped zinc oxide nanoparticles were derived by simple chemical co-15 precipitation route using zinc acetate dihydrate and cadmium acetate dehydrate as 16 precursor materials. The thick films were casted from chemical co-precipitation route 17 prepared nanoparticles by economic facile screen printing method. The structural, mor-18 phological, optical and electrical properties of the film were characterized relevant to 19 alcohol vapor sensing application by powder XRD, SEM, UV-VIS and DC conductivity 20 techniques. The response and sensitivity of alcohol (ethanol) vapor sensor are obtained 21 22 from the recovery curves at optimum working temperature range from 20° C to 50° C. The result shows that maximum sensitivity of the sensor is observed at $25^{\circ}C$ operating 23 24 temperature. On varying alcohol vapor concentration, minor variation in resistance has been observed. The sensing mechanism of sensor has been described in terms of physical 25 adsorption and chemical absorption of alcohol vapors on cadmium-doped zinc oxide film 26 surface and inside film lattice network through weak hydrogen bonding, respectively. 27

28 Keywords: Doped zinc oxide; alcohol; sensor; thick films.

²⁹ 1. Introduction

Nanocrystalline transparent metal oxide semiconductors have drawn considerable 30 attention of researchers due to their unique physical, chemical and optical prop-31 erties. Zinc oxide (ZnO) belongs to the class of wide-bandgap semiconducting 32 material ($E_q \sim 3.3 \text{ eV}$) of n-type nature with hexagonal wurtzite structure and 33 60 meV binding energy and find practical applications in the field of sensors,¹⁻⁴ 34 varistors, electro-optic^{5,6} and microelectronic devices.^{7–10} The stability of ZnO film 35 has made it suitable alternative candidate to tin oxide and indium tin oxide films 36 whose electrical and optical properties degrades in hydrogen plasma. Nowadays 37

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